MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK040N60Z1

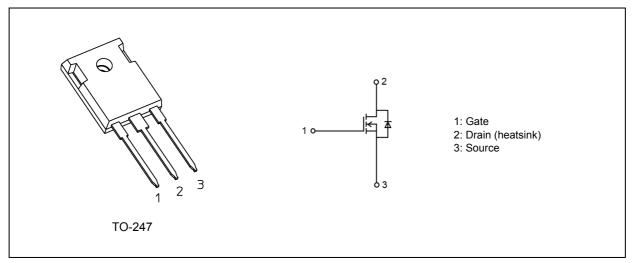
1. Applications

• Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.033 \Omega$ (typ.)
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode: V_{th} = 3 to 4 V (V_{DS} = 10 V, I_D = 2.4 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | |
|---|----------|------------------|------------|-------|
| Drain-source voltage | | V _{DSS} | 600 | V |
| Gate-source voltage | | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | Ι _D | 52 | A |
| Drain current (pulsed) | (Note 1) | I _{DP} | 208 | |
| Power dissipation $(T_c = 25 \text{ °C})$ | | PD | 297 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 1049 | mJ |
| Single-pulse avalanche current | | I _{AS} | 8.0 | A |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 52 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 208 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |
| Mounting torque | | TOR | 0.8 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2024-06

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.420 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 50 | |

Note 1: Ensure that the channel temperature does not exceed 150 °C. Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 29 mH, I_{AS} = 8.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

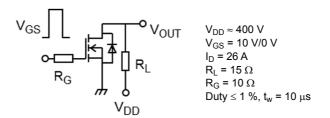
6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

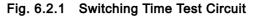
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|-------|-------|------|
| Gate leakage current | I _{GSS} | V_{GS} = ±30 V, V_{DS} = 0 V | _ | _ | ±1 | μA |
| Drain cut-off current | I _{DSS} | V_{DS} = 600 V, V_{GS} = 0 V | _ | — | 2 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | — | — | V |
| Gate threshold voltage | V _{th} | V _{DS} = 10 V, I _D = 2.4 mA | 3 | _ | 4 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 21.2 A | | 0.033 | 0.040 | Ω |

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------|--------------------|---|-----|------|-----|------|
| Input capacitance | | C _{iss} | V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz | _ | 5200 | _ | pF |
| Reverse transfer capacitance | | C _{rss} |] | _ | 4.0 | _ | |
| Output capacitance | | C _{oss} |] | _ | 120 | _ | |
| Effective output capacitance (energy related) | (Note 3) | C _{o(er)} | V_{DS} = 0 to 400 V, V_{GS} = 0 V | — | 200 | — | |
| Effective output capacitance (time related) | (Note4) | C _{o(tr)} | V_{DS} = 0 to 400 V, V_{GS} = 0 V | — | 1450 | — | |
| Gate resistance | | rg | V _{DS} = OPEN , f = 1 MHz | _ | 2.4 | _ | Ω |
| Switching time (rise time) | | t _r | See Fig.6.2.1 | | 75 | _ | ns |
| Switching time (turn-on time) | | t _{on} |] | _ | 120 | _ | |
| Switching time (fall time) | | t _f |] | | 5 | _ | |
| Switching time (turn-off time) | | t _{off} | 1 | _ | 150 | _ | |
| MOSFET dv/dt ruggedness | | dv/dt | $V_{DS} \leq V_{DSS}, \ I_D \leq 26 \ A$ | 120 | _ | _ | V/ns |

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 V to 400 V. Note4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 V to 400 V.





6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400$ V, V_{GS} = 10 V, I_{D} = 52 A | — | 85 | — | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 29 | _ | |
| Gate-drain charge | Q _{gd} | | _ | 22 | | |

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|------------------|---|-----|------|------|------|
| Diode forward voltage | V _{DSF} | I _{DR} = 52 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | V _{DD} = 400 V, | _ | 380 | _ | ns |
| Reverse recovery charge | Q _{rr} | I _{DR} = 26 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs | _ | 6.7 | _ | μC |
| Peak reverse recovery current | I _{rr} | $-di_{DR}/dt = 100 A/\mu s$ | _ | 35 | _ | А |
| Diode dv/dt ruggedness | dv/dt | $V_{DD} \leq 400$ V, $I_{DR} \leq 26$ A, V_{GS} = 0 V | 50 | | _ | V/ns |

7. Marking (Note)

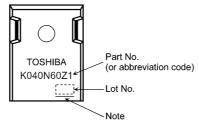


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

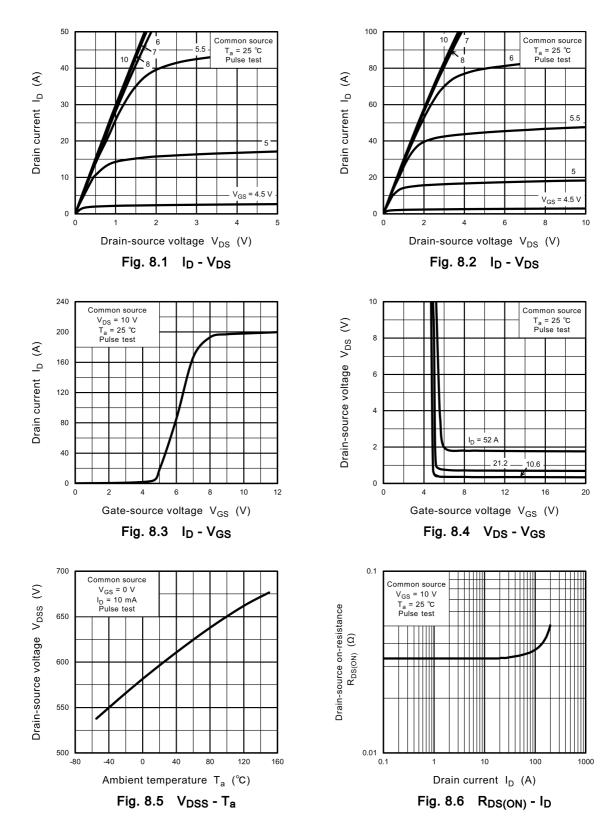
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

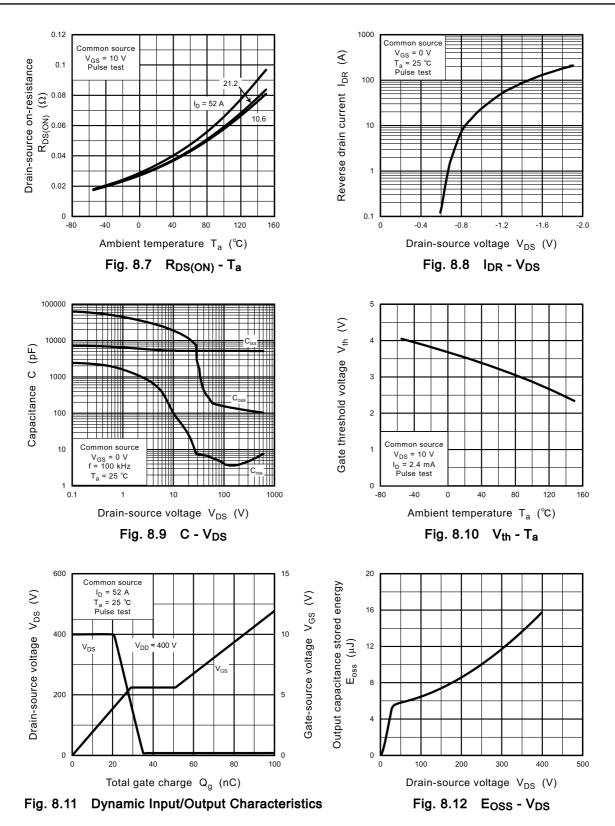
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

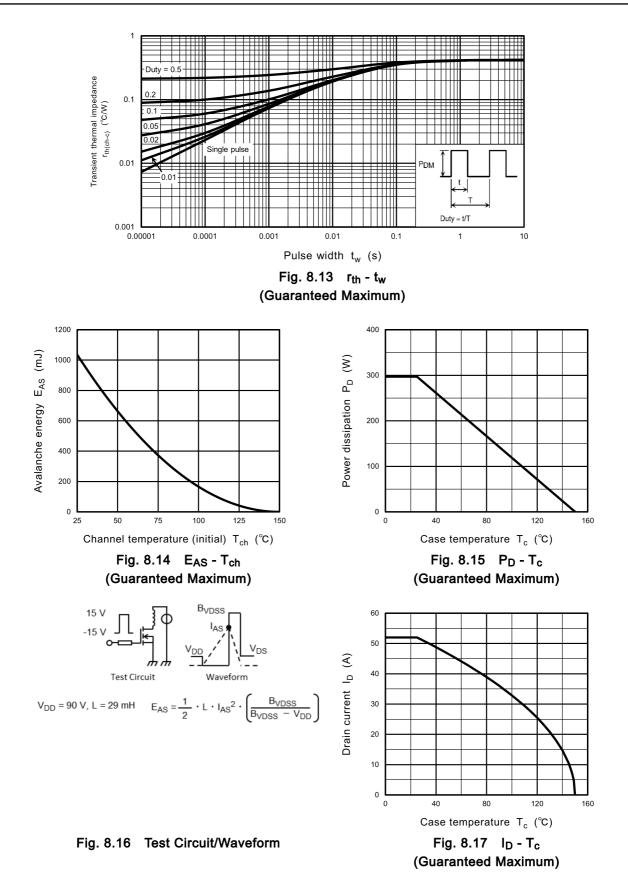
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

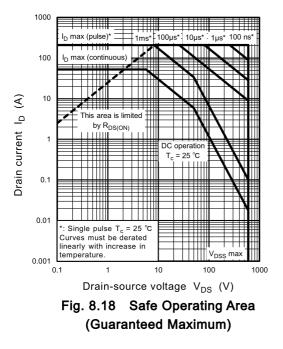
8. Characteristics Curves (Note)









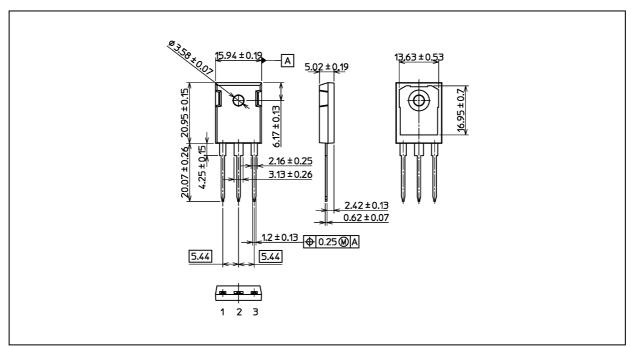


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TK040N60Z1

Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

| | Package Name(s) |
|------------------|-----------------|
| TOSHIBA: 2-16L1A | |
| Nickname: TO-247 | |

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